

BORON OXIDE Doped Silicon Wafer

Product Description

Silicon wafer-Silicon substrate is a thin slice of semiconductor material. It is used in electronics for the fabrication of integrated circuits and in photovoltaics for conventional, wafer-based solar cells. It is used as a support for the manufacture of microstructures by techniques such as etching, doping, deposition of other materials (epitaxy, sputtering, chemical vapor deposition, etc.) and photolithography.

- Totally customized
- Low and medium volumes
- Any diameter
- Any orientations
- Any thickness

Typical Properties

Dopant	:	Boron Oxide
Crystal Orientation	:	< 100>
Type	:	P
Growth Method	:	CZ
Resistivity	:	1.0-5.0Ω.cm
TTV	:	<10.0μm
STIR	:	<2μm
GLOBAL TIR	:	<5μm

Applications

- ✓ R&D and manufacturing
- ✓ Resistive touch panel application
- ✓ Automobiles, aerospace and drone technology
- ✓ AI (Artificial Intelligence)
- ✓ MEMS fabrication
- ✓ Transistors, diodes, and rectifiers
- ✓ Robotics
- ✓ Solar cell
- ✓ MEMS, Biotechnology
- ✓ Optical sensors

Key Features

Product	:	Boron Oxide Doped Silicon Wafer
Stock No	:	NS6130-10-1085
CAS	:	7440-21-3
Diameter	:	2"
Thickness	:	275μm



NS6130-10-1085

2"
Inch
P Type

Follow us:

[f](#) [@](#) [t](#) [in](#) | www.nanoshel.com | sales@nanoshel.com

